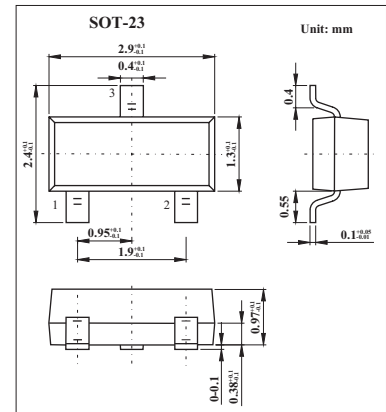


## Low-leakage double diode

## BAW156

## ■ Features

- Plastic SMD package
- Low leakage current: typ. 3 pA
- Switching time: typ. 0.8  $\mu$  s
- Continuous reverse voltage: max. 75 V
- Repetitive peak reverse voltage: max. 85 V
- Repetitive peak forward current: max. 500 mA.

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Conditions	Min	Max	Unit
Repetitive peak reverse voltage	$V_{RRM}$			85	V
Continuous reverse voltage	$V_R$			75	V
Continuous forward current	$I_F$	single diode loaded; note 1		160	mA
		double diode loaded; note 1		140	
Repetitive peak forward current	$I_{FRM}$			500	mA
Non-repetitive peak forward current	$I_{FSM}$	square wave; $T_j = 25^\circ\text{C}$ prior to surge			A
		$t = 1 \mu\text{s}$		4	
		$t = 1 \text{ms}$		1	
		$t = 1 \text{s}$		0.5	
Total power dissipation	$P_{tot}$	$T_{amb} \leq 25^\circ\text{C}$ ; note 1		250	mW
Storage temperature	$T_{stg}$		-65	+150	$^\circ\text{C}$
Junction temperature	$T_j$			150	$^\circ\text{C}$
thermal resistance from junction to tie-point	$R_{th\ j-t\ p}$			360	K/W
thermal resistance from junction to ambient	$R_{th\ j-a}$			500	K/W

Note

1. Device mounted on an FR4 printed-circuit board.

**BAW156**■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Conditions	Typ	Max	Unit
Forward voltage	$V_F$	$I_F = 1\text{ mA}$		900	mV
		$I_F = 10\text{ mA}$		1000	
		$I_F = 50\text{ mA}$		1100	
		$I_F = 150\text{ mA}$		1250	
Reverse current	$I_R$	$V_R = 75\text{ V}$	0.003	5	nA
		$V_R = 75\text{ V}; T_j = 150^\circ\text{C}$	3	80	
Diode capacitance	$C_d$	$f = 1\text{ MHz}; V_R = 0$	3		pF
Reverse recovery time	$t_{rr}$	when switched from $I_F = 10\text{ mA}$ to $I_R = 10\text{ mA}$ ; $R_L = 100\ \Omega$ ; measured at $I_R = 1\text{ mA}$ ;	0.8	3	$\mu\text{ s}$

## ■ Marking

Marking	JZp
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